

MMG450WB060B6EN

600V 450A IGBT Module

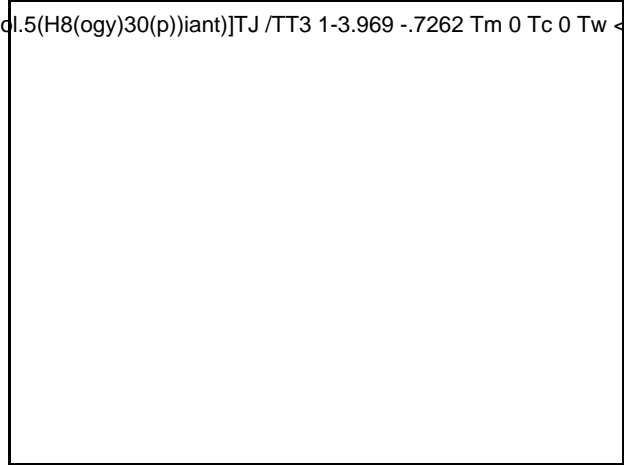
April 2017

Version 2

RoHS Compliant

PRODUCT FEATURES

IGBT³ CHIPMsT(3.3Bo)43ch+Fi.5(H8(el.5(H8(d St.5(l)op t.5(l)e)H8(chnd.5(H8(ogy)30(p))iant))TJ /TT3 1-3.969 -.7262 Tm 0 Tc 0 Tw <01b6>Tj /T



APPLICATIONS

Unit

W

ABSOLUTE MAXIMUM RATINGS (T_C=25°C unless otherwise specified)

				Unit
I _{F(AV)}	Average Forward Current		450	V
I _{FRM}	Repetitive Peak Forward Current	tp=1ms	900	A
I ² t		T _J =125 , t=10ms, V _R =0V	12.5	KA ² S

Unit

mA

mA

nA

μ C

nF

pF

ns

ns

ns

ns

ns

500

ns

ns

t_f

25

ns

Unit
K
K

Unit

MMG450WB060B6EN

$I_c(A)$

$E_{on}E_{off}$

$V_{GE} \text{ \AA V \AA}$

$R_g \text{ \AA \AA}$

Figure 3. Typical Transfer characteristics IGBT-inverter

Figure 4. Switching Energy vs Gate Resistor IGBT-inverter

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$V_F(V)$

Figure 9. Diode Forward Characteristics Diode -inverter

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$R_g \text{ } \mu\text{s}$

Figure 10. Switching Energy vs Gate Resistor Diode -inverter

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Figure 14. Circuit Diagram

Dimensions in (mm)